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Magnetoresistive conductive polymer-tungsten trioxide nanocomposites with ultrahigh sensitivity at low magnetic field



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ABSTRACT

The effect of conductive polymer matrix including polyaniline (PANI) and polypyrrole (PPy) on the magnetoresistance (MR) behaviors in the variable range hopping (VRH) regime has been investigated in the disordered polymer nanocomposites containing tungsten trioxide (WO₃) nanoparticles. These nanocomposites have demonstrated ultrahigh MR sensitivity at low magnetic field regime. The observed positive MR has been well explained by the wave-function shrinkage model. The conductive polymer matrix has shown different effects on the MR behaviors of the nanocomposites. The WO₃/PANI nanocomposites have a lower localization length (a_0) and density of states at the Fermi level ($N(E_F)$), and higher average hopping distance (R_{hop}) and average hopping energy (W) compared with those of the WO₃/PPy nanocomposites.

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1. Introduction

The magnetoresistance (MR) phenomenon, defined as $\Delta R/R = [R(B) - R(0)]/R(0)$, describes the resistance change of a material under an applied external magnetic fields [1]. Since the first discovery of huge MR change, which is called giant magnetoresistance (GMR) effect, in the thin-film structural metallic materials composed of a pair of ferromagnetic layers (Fe) separated by a non-magnetic metal layer (Cr) in 1988 [2,3], GMR-based electronics have been developed and widely used in the areas including rotation speed sensing, angular position sensing, biosensors and biochips, magnetic field sensors, hard disc drivers and magnetic random access memory (MRAM) in computers [4,5]. In the last decade, the GMR effect in conductive polymers and their nanocomposite systems has attracted intense interests due to their easy synthesis, low cost, high conductivity and

relatively high GMR signals compared with other organic semiconductors [5.6]. For example, around 95% GMR has been reported in the magnetic p-toluene sulfonic acid (PTSA) doped polyaniline (PANI) nanocomposites with a Fe₃O₄ nanoparticle loading of 30 wt% synthesized using surface initiated polymerization (SIP) method and 53% GMR in the PTSA doped pure PANI [1]. About 20% of GMR in the non-magnetic PANI nanocomposites with a BaTiO₃ (~500 nm) loading of 20 wt% synthesized by SIP method and around 35% GMR in the 20 wt% BaTiO₃ (~500 nm)/ PANI nanocomposites prepared by simple physical mixture of PANI and BaTiO₃ powders have been reported [7]. Later on, up to 95.5% GMR was reported in the phosphoric acid (H₃PO₄) doped non-magnetic PANI nanocomposites with 20 wt% silica nanoparticle loading and 65.6 wt% GMR in the H₃PO₄ doped pure PANI [8]. Meanwhile, a GMR effect of around 22% in the non-magnetic silicon/PANI nanocomposites was reported [9]. In addition, a room temperature MR transition from positive to negative has been reported in the silicon/PANI nanocomposites with a silicon loading of 10 wt% in the variable range hopping (VRH) regime and the wave-function shrinkage model and forward interference model have been used to separate the positive and negative MR from the obtained MR results [10].

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Conducting polymers, such as polyacetylene (PA), PANI, polypyrrole (PPy), polythiophenes (PTs) and poly(DNTD), have gained more attentions in the last few decades [11] since the first discovery of the electrical conduction in doped PA [12]. They have been widely used in the applications including electronics [13], fire retardants [14], electrodes for electrodeposition [15] and supercapacitors [16,17]. Tungsten trioxide (WO₃), a n-type semiconductor with a band gap of 2.7 eV, has been widely used in electrochromic devices [16], photocatalysts [17], gas sensors [18], fuel cell catalyst support [19], and photochromic process [20] due to its good chemical stability and genuine color switching. PANI and PPy are two most used conducting polymers due to their easy synthesis and doping/ dedoping process [21]. Even though the PANI and PPy nanocomposites with WO₃ nanoparticles have been synthesized using a surface initiated polymerization (SIP) method [22,23], the MR behaviors of these nanocomposites have not been reported yet so far.

In this paper, the effect of conductive polymer matrix including PANI and PPy on the GMR behaviors of the non-magnetic disordered conductive polymer nanocomposites with different WO_3 nanoparticle loading in the disordered VRH regime is investigated. The morphology and crystallization structure of the synthesized $WO_3/PANI$ and WO_3/PPy nanocomposites are studied. The ultrahigh MR sensitivity at low magnetic field in these nanocomposites is analyzed by the wave-function shrinkage model.

2. Experimental

2.1. Materials

Aniline (C_6H_7N), pyrrole (C_4H_5N) and ammonium persulfate (APS, (NH₄)₂S₂O₈), and p-toluene sulfonic acid (PTSA, $C_7H_8O_3S$) were purchased from Sigma Aldrich. The WO₃ nanoparticles (99+%) with an average diameter of 30 nm were obtained from Nanostructured & Amorphous Materials, Inc. All the chemicals were used as-received without any further treatment.

2.2. Preparation of WO₃/PANI and WO₃/PPy nanocomposites

The WO₃/PANI and WO₃/PPy nanocomposites were fabricated using SIP method. A certain amount of WO₃ nanoparticles was mixed in a solution of PTSA and APS with a ratio of 15 mmol: 9 mmol in 100 mL deionized water in an ice-water bath for 1 h sonication combined with mechanical stirring. The aniline or pyrrole solution (18 mmol in 25 mL deionized water with molar ratio of PTSA: APS: aniline = 5: 3: 6) was mixed with the above solution and then sonicated and mechanically stirred for additional 1 h in an ice-water bath for polymerization. The product was vacuumfiltered and washed with deionized water several times to remove any unreacted PTSA and APS. The precipitant was further washed with methanol to remove any possible oligomers. The final product was dried at 50 °C in an oven overnight. The WO₃/PANI nanocomposites with a WO₃ loading of 10, 20, 40 and 60 wt% and the WO₃/PPy nanocomposites with a WO₃ loading of 40 and 60 wt% were prepared following the above procedure.

2.3. Characterizations

The morphology of the as-received WO₃ nanoparticles and synthesized nanocomposites was examined in the field emission scanning electron microscope (SEM, JEOL, JSM-6700F). The morphology and nanoparticle distribution were further obtained in a Philips CM-200 transmission electron microscopy (TEM) with a LaB6 filament. The samples were prepared by drying a drop of nanocomposite powders ethanol suspension on carbon-coated copper TEM grids.

X-ray diffraction (XRD) analysis was carried out with a Bruker AXS D8 Discover diffractometer with GADDS (General Area Detector Diffraction System) operating with a Cu-K α radiation source filtered with a graphite monochromator ($\lambda = 1.5406 \text{ Å}$).

The resistivity (ρ) was measured by a standard four-probe method from 100 to 290 K. The sample was prepared by pressing WO₃/PANI and WO₃/PPy nanocomposite powders to disc pellet form with a diameter of 25 mm by applying a pressure of 50 MPa in a hydraulic presser and the average thickness was about 1.0 mm. The temperature dependent resistivity was used to determine the electrical conduction mechanism in the WO₃/PANI and WO₃/PPy nanocomposites. The same sample was used for the dielectric property test by a LCR meter (Agilent, E4980A) equipped with a dielectric test fixture (Agilent, 16451B) at the frequency range of 20 to 2 \times 10⁶ Hz at room temperature under the alternative electric field.

The same sample was also used for MR measurements using a standard four-probe technique by a 9-T Physical Properties Measurement System (PPMS) by Quantum Design at room temperature. The four probes were 0.002 inch diameter platinum wires, which were attached by silver paste to the sample. And the magnetic field was applied perpendicular to the current.

3. Results and discussions

3.1. Microstructure observations

The SEM and TEM of 10.0 wt% loading of WO₃/PANI and WO₃/ PPv nanocomposites are shown in Fig. 1 and Fig. S1, respectively. The as-received WO₃ nanoparticles, Fig. 1(a), exhibit a ball-like structure and the surface is very smooth. However, after coated with PANI and PPy, the nanocomposites show very different morphologies from the as-received nanoparticles. Fig. 1(b&c) shows the SEM images of 10.0 wt% loading of WO₃/PANI and WO₃/PPy nanocomposites, respectively. The 10.0 wt% loading of WO₃/PANI nanocomposites show very rough surface, Fig. 1(b), indicating the polymerization of the aniline on the surface of the WO₃ nanoparticles [24]. The 10.0 wt% loading of WO₃/PPy nanocomposites exhibit the particulate microstructure as that of the as-received WO₃ nanoparticles, Fig. 1(c). It is obvious that the diameters of the 10.0 wt% loading of WO₃/PPy nanocomposites are much bigger than that of the as-received WO₃ nanoparticles, illustrating the polymerization of the pyrrole on the surface of WO₃ nanoparticles. The TEM images in Fig. S1 show the good dispersion of the nanoparticles within the polymer matrix and a uniform coating layer of polymer outside the nanoparticles is observed. FT-IR results of the synthesized WO₃/PANI and WO₃/PPy nanocomposites are shown in Fig. S2&S3, respectively. The characteristic peaks of PANI and PPy are observed obviously in the FT-IR spectra, which further confirms that the PANI and PPy present on the surface of WO₃ nanoparticles.

3.2. X-ray diffraction

The crystallization structures of the as-received WO₃ nanoparticles and the synthesized WO₃/PANI and WO₃/PPy nanocomposites are determined by X-ray diffraction (XRD), Fig. 2. The observed strong intensity of the diffraction peaks in the XRD test of all the samples indicates the highly crystallized structure [22]. The diffraction peaks at around $2\theta = 23.1, 23.65, 24.4, 26.6, 28.8, 33.35, 34.2, 41.55, 47.35, 50.0$ and 55.95° in the as-received WO₃ nanoparticles, Fig. 2(b), correspond to the (0 0 2), (0 2 0), (2 0 0), (1 2 0), (1 1 2), (0 2 2), (2 0 2), (2 0 1), (2 1 1), (2 2 0) and (2 2 2) crystallographic planes of the crystallized WO₃ nanoparticles [25]. The broad peak at around 20° in the 10 wt% loading of WO₃/PANI nanocomposites is attributed to the crystallographic planes of the

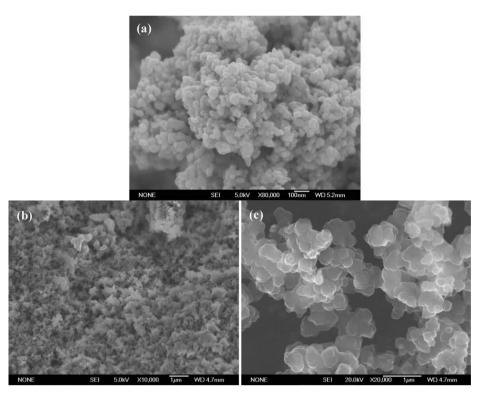


Fig. 1. SEM microstructures of (a) as-received WO₃ nanoparticles, (b) 10.0 wt% loading of WO₃/PANI, and (c) 10 wt% loading of WO₃/PPy.

partially crystallized PANI [26] and the intensity of this broad peak decreases and even disappears with increasing the WO₃ nanoparticle loading in the WO₃/PANI nanocomposites, Fig. 2(a, c, d & e).

The average crystallite size is estimated through XRD pattern using the Scherrer Equation (1) [1]:

$$\beta = \frac{k\lambda}{L\cos\theta} \tag{1}$$

where λ is the X-ray wavelength ($\lambda=0.154$ nm), L is the average crystallite size, k is the shape factor, β is the full-width at half-maximum, and θ is Bragg angle in degree. The shape factor k, which depends on several factors including the miller index of the reflection plane and the shape of the crystal, normally is 0.89. The peak at $2\theta=28.8^\circ$ is chosen to calculate the average crystallite size. The obtained average crystallite size of the WO₃ nanoparticles is about 29.4 nm. In the WO₃/PANI nanocomposites, the calculated average crystallite size is 25.0, 25.1, 27.0 and 29.5 nm for the WO₃/

PANI with a WO $_3$ loading of 10, 20, 40 and 60 wt%, respectively. The average crystallite size is 24.9 and 28.7 nm for the WO $_3$ /PPy with a WO $_3$ loading of 40 and 60 wt%, respectively. There is little change of the average crystallite size of WO $_3$ nanoparticles after fabrication of the conducting polymer nanocomposites.

3.3. Temperature dependent resistivity-electrical conduction mechanism

The temperature dependent resistivity for the WO₃/PANI and WO₃/PPy nanocomposites is shown in Fig. 3(a&c). The resistivity of all the synthesized samples decreases with increasing temperature, exhibiting a semiconductor behavior from 50 to 290 K [27]. In Fig. 3(a), the resistivity of WO₃/PANI nanocomposites obeys the following relationships: 40 wt% WO₃/PANI > 60 wt% WO₃/PANI > 10 wt% WO₃/PANI > 20 wt% WO₃/PANI. Higher resistivity is observed in the PANI nanocomposites after the WO₃ loading

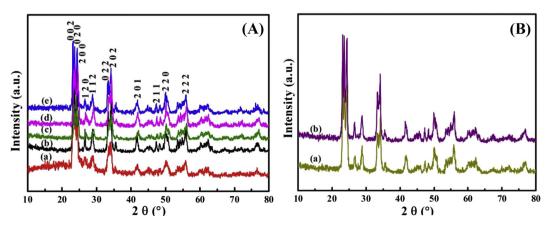


Fig. 2. XRD of the (A) WO₃/PANI nanocomposites with a WO₃ loading of (a) 10, (c) 20, (d) 40, (e) 60 wt% and (b) as-received WO₃ nanoparticles; (B) WO₃/PANI nanocomposites with a WO₃ loading of (a) 40 and (b) 60 wt%.

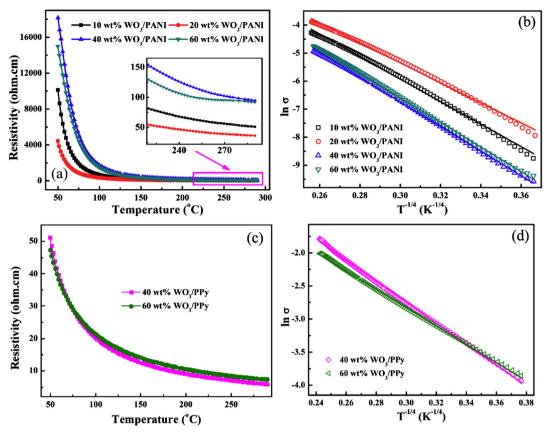


Fig. 3. Resistivity vs. temperature for the (a) WO₃/PANI and (c) WO₃/PPy nanocomposites; and $\ln(\sigma)$ and $T^{-1/4}$ curves for (b) WO₃/PANI and (d) WO₃/PPy nanocomposites.

increases to 40 wt% due to the percolation of the WO3 nanoparticles. Therefore, the resistivity of WO₃/PANI with a WO₃ nanoparticle loading of 40 and 60 wt% are very close to each other but higher than that of the WO₃/PANI nanocomposites with a WO₃ nanoparticle loading of 10 and 20 wt%. This is also observed in the Fe₃O₄/PANI nanocomposites, in which the resistivity decreases with increasing the nanoparticle loading to 16.67 wt% and increases dramatically as the nanoparticle loading increases to 30 wt% [1]. The resistivity for the WO₃/PANI nanocomposites with a WO₃ loading of 10, 40 and 60 wt% is decreased by almost 4 orders of magnitude as the temperature increases from 50 to 290 K and the resistivity of the 20 wt% loading of WO₃/PANI nanocomposites has 3 orders of magnitude decrease within the temperature range of 50~290 K. At temperature of 290 K, the highest resistivity of 94.66 Ω.cm is observed in the 40 wt% loading of the WO₃/PANI nanocomposites and the lowest resistivity of 36.17 Ω cm is obtained in the 20 wt% loading of WO₃/PANI nanocomposites. In Fig. 3(c), the resistivity of the WO₃/PPy nanocomposites with a WO₃ loading of 40 and 60 wt% is very similar to each other, which only has a small change from 51.08 to 5.99 Ω.cm for 40 wt% WO₃/PPy nanocomposites and from 47.31 to 7.46 Ω.cm for 60 wt% WO₃/PPy nanocomposites with the temperature increasing from 50 to 290 K.

The electrical conduction mechanism is investigated through the obtained temperature dependent resistivity using Mott VRH approach, which is expressed as Equation (2) [27]:

$$\sigma = \sigma_0 \exp\left[-\left(\frac{T_0}{T}\right)^{1/n+1}\right] \tag{2}$$

where the constant σ_0 stands for the conductivity at infinite low temperature, T(K) is the Kelvin temperature, and constant $T_0(K)$ is

the hopping barrier, which stands for the characteristic Mott temperature and is described as Equation (3) [28]:

$$T_0 = \frac{24}{\pi k_{\rm B} N(E_{\rm F}) a_0^3} \tag{3}$$

where a_0 is the localization length, $k_{\rm B}$ is Boltzmann constant and $N(E_{\rm F})$ is the density of states at the Fermi level. The value n is the dimension of the system and n=3, 2 and 1 stands for 3-, 2- and 1-dimensional systems, respectively [29]. The σ_0 and T_0 can be obtained from the intercept and slope of the linear fitting $\ln(\sigma) \sim T^{-1/(n+1)}$. In the Mott's VRH mechanism, T_0 , a_0 , average hopping distance $(R_{\rm hop})$, and average hopping energy (W) are important characteristic parameters. And $R_{\rm hop}$ and W can be expressed as Equations (4) and (5), respectively:

$$R_{\text{hop}} = \left(\frac{3}{8}\right) \left(\frac{T_0}{T}\right)^{1/4} a_0 \tag{4}$$

$$W = \frac{3}{4\pi R_{\text{hop}}^3 N(E_{\text{F}})} \tag{5}$$

The best linear fits of $\ln(\sigma) \sim T^{-1/(n+1)}$ for the WO₃/PANI and WO₃/PPy nanocomposites obtained from Fig. 3(a&c) are shown in Fig. 3(b&d) with n=3 in the temperature range of $50 \sim 290$ K, indicating that the synthesized WO₃/PANI and WO₃/PPy nanocomposites obey quasi 3D VRH hopping mechanism. This means that all the synthesized nanocomposites are disordered system in 3D VRH regime. The calculated σ_0 and T_0 are listed in Table 1. The nanocomposites with the WO₃ loading of higher than 40 wt% behave more like a disordered metal than a disordered polymer.

And the conductivity of the 3D disordered metals can be fitted by Equation (6) [30]:

$$\sigma = \sigma_0 + AT^{1/2} + BT^{p/2} \tag{6}$$

where the second term arises from the electron—electron interactions and the third term is related to σ_0 due to the weak localization effects. In the disordered system, the electron—electron interactions play an important role in the low-temperature electrical transport and the weak localization effects are predominant at the higher temperature. For the 2D disordered system, the conductivity is related to the logarithmic temperature for both the electron—electron interaction and weak localization, which can be expressed as Equation (7) [31,32]:

$$\sigma = \sigma_0 + C \ln T \tag{7}$$

However, the conducting polymer nanocomposites in this work were synthesized by a SIP method and the PANI and PPy have been coated on the surface of nanoparticles. Even for the high loading of WO₃ (such as 40 and 60 wt%) in the nanocomposites, the PANI and PPy still can be observed on the surface of WO₃ as confirmed from FT-IR analysis in Fig. S2&S3. The conductivity in these systems is dominated by the PANI or PPy phase rather than the metal oxide phase. Therefore, the conductivity is fitted by Mott's law in this work to obtain the important parameter T_0 .

3.4. Room temperature magnetoresistance

The room temperature MR result for the synthesized WO₃/PANI and WO₃/PPy nanocomposites calculated from MR = (R(H) −R(0))/R(0) is shown in Fig. 4(a)&(b), respectively. For the WO₃/PANI nanocomposites, Fig. 4(a), the MR shows positive values within the measured magnetic field range and magnetic field (H) dependent behaviors. The MR of the WO₃/PANI nanocomposites shows the following relationships: 20 wt% WO₃/PANI < 10 wt% WO₃/PANI < 60 wt% WO₃/PANI < 40 wt% WO₃/PANI. The MR value of up to 32.63% is observed in the 40 wt% WO₃/PANI nanocomposites at an H of 7 T. Only 1.65% MR value is obtained for the 20 wt% WO₃/PANI nanocomposites at an H of 7 T. In Fig. 4(b), the MR of the WO₃/PPy nanocomposites also shows positive values in the measured H range. At the same loading of WO₃ nanoparticles, the MR values of the WO₃/PPy nanocomposites are smaller than that of the WO₃/PANI nanocomposites at the same H, which indicates that the polymer matrix can affect the MR behavior of the nanocomposites. Generally, the magnetic field sensor is based on the MR effect and the MR can be used to present the sensitivity of the materials to the H [33]. Thus, the sensitivity of a material to the applied H can be expressed as either MR value at the low H or linear with respect to the H (i.e. slope at low H) [34,35]. The slope of the MR curves for the WO₃/PANI nanocomposites with a WO₃ nanoparticle loading of 10, 20, 40 and 60 wt% is 12.205, 3.434, 163.367 and 134.703 (the corresponding MR value at H of 1 T for WO₃/PANI nanocomposites with a WO₃ nanoparticle loading of 10, 20, 40 and

Table 1 T_0 and σ_0 for the WO₃/PANI and WO₃/PPy nanocomposites.

Samples	<i>T</i> ₀ (K)	σ_0 (S cm ⁻¹)
WO₃/PANI nanocomp	osites	
10 wt%	2.60×10^{6}	456.04
20 wt%	1.62×10^{6}	212.55
40 wt%	3.72×10^{6}	622.78
60 wt%	3.75×10^{6}	744.91
WO ₃ /PPy nanocompo.	sites	
40 wt%	6.29×10^{4}	7.45
60 wt%	3.67×10^4	3.76

60 wt% is 1.1, 0.3, 17.12 and 13.80%, respectively), respectively. For the WO₃/PPy nanocomposites with a WO₃ nanoparticle loading of 40 and 60 wt%, the slope of MR curves is 14.351 and 18.213, respectively. Therefore, the WO₃/PANI nanocomposites with a WO₃ nanoparticle loading of 40 wt% have the highest sensitivity to the magnetic field and 20 wt% loading of WO₃/PANI nanocomposites have the lowest sensitivity to the magnetic field. The room temperature MR results of pure PANI and pure PPy were reported in our previous papers [1,28] and they are shown in Fig. S4. From Fig. S4, the MR of pure PANI and PPy is observed to be very different. Pure PANI has very high MR value of 53% at a magnetic field of 9 T and pure PPy has a lower MR value around 0.4% at a magnetic field of 9 T. This also indicates the polymer matrix effect on the MR property.

Generally, for the highly disorderedly localized systems in the VRH regime, the wave-function shrinkage model is often introduced to illustrate the observed positive MR effect [10]. In the wave-function shrinkage model, the common idea is based on the contraction of the electronic wave function at impurity centers in the magnetic field, leading to a reduction in the hopping probability between two sites and causing a positive MR. The $r_{\text{wave}} = R(H,T)/R(0,T)$ is described as Equation (8) [10]:

$$r_{\text{wave}} = \exp\{\xi_C(0)[\xi_C(H)/\xi_C(0) - 1]\}$$
 (8)

where $\xi_C(0) = (T_0/T)^{1/4}$ for the 3D Mott VRH mechanism, $\xi_C(H)$ is the optimum hopping probability parameter, $\xi_C(H)/\xi_C(0)$ is the normalized hopping probability parameter and as a function of H/P_C for Mott VRH mechanism, P_C is the fitting parameter given by Equation (9):

$$P_c = 6\hbar/\left[ea_0^2\xi_C(0)\right] \tag{9}$$

where e is electron charge, a_0 is the localization length, \hbar is reduced Planck's constant and T_0 is Mott characteristic temperature. In the low-field limit (<1 T), the r_{wave} can be expressed as Equation (10):

$$r_{\text{wave}} \approx 1 + t_2 \frac{H^2}{P_{\text{C}}^2} \left(\frac{T_0}{T}\right)^{1/4}$$
 (10)

i.e. Equation (11):

$$MR = \frac{\Delta R(H,T)}{R(0,T)} \approx t_2 \frac{H^2}{P_C^2} \left(\frac{T_0}{T}\right)^{1/4} = t_2 \frac{e^2 a_0^4}{36\hbar^2} \left(\frac{T_0}{T}\right)^{3/4} H^2$$
 (11)

where the numerical constant $t_2 \approx 5/2016$ [36]. In Fig. 4(a), the MR of all the synthesized nanocomposites is observed to sharply increase with increasing H for H increasing to 0.1 T and then shows the quadratic H^2 dependent property. In the wave-function shrinkage model, this magnetic field dependent behavior has been explained as follows: in the low magnetic field, the applied H decreased the overlap probability between two sites, resulting in an increased resistance with an increased H [34]; in the higher magnetic field, the variable range hopping between the localized states having a Coulomb gap in the density of states at the Fermi level, which causes the quadratic H dependent behavior [35].

Thus, the a_0 can be calculated from T_0 , MR and H from following Equation (12):

$$a_0^4 = \frac{36\hbar^2 MR}{t_2 e^2} \left(\frac{T_0}{T}\right)^{-3/4} H^{-2} \tag{12}$$

For example, the obtained a_0 for the 10 wt% WO₃/PANI nanocomposites at 290 K is 61.2, 30.8, and 24.4 nm for H at 1.0, 5.0, and 9.0 T, respectively. The calculated a_0 for the WO₃/PANI and WO₃/

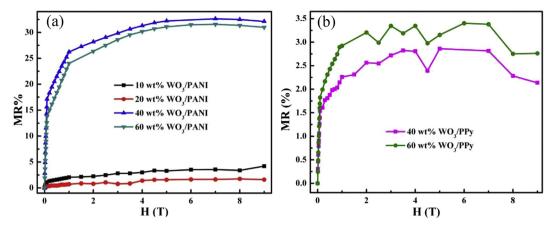


Fig. 4. Room temperature magnetoresistance (a) WO₃/PANI and (b) WO₃/PPy.nanocomposites.

PPy nanocomposites at different H is listed in Table 2. From the calculated results, the a_0 is observed to have H dependent property after applying an external H and decreases with increasing H. After obtaining a_0 , the $N(E_{\rm F})$ can be calculated from Equation (13) [37]:

$$N(E_{\rm F}) = \frac{24}{\pi k_{\rm B} T_0 a_0^3} \tag{13}$$

The calculated corresponding $N(E_{\rm F})$ is also listed in Table 2 and the $N(E_{\rm F})$ has a H dependent behavior and increases with increasing H. The calculated average hopping length $R_{\rm hop}$ and average hopping energy W for the WO₃/PANI and WO₃/PPy nanocomposites are shown in Table 2, respectively. The calculated $R_{\rm hop}$ (nm) has the H dependent behavior and decreases with increasing H. Generally, the positive MR in the hopping system is due to the charge carrier hopping conduction arising from the contraction of the charge carrier wave function and the subsequent reduced $R_{\rm hop}$ [27]. This phenomenon is also observed in the silica/PANI [8], silicon/PANI [9]

Table 2 a_0 , $N(E_{\rm F})$, $R_{\rm hop}$ and W for the WO₃/PANI and WO₃/PPy nanocomposites at different magnetic field H.

Samples	Parameters	Magnetic field H (T)		
		1.0	5.0	9.0
WO ₃ /PANI				
10 wt%	$a_0 (nm)$	61.2	30.8	24.4
	$N(E_{\rm F})~({\rm eV}~{\rm cm}^3)^{-1}$	1.49×10^{14}	1.17×10^{15}	2.35×10^{15}
	R_{hop} (nm)	223.3	112.4	89.0
	W (meV)	144.1	144.1	144.1
20 wt%	a_0 (nm)	51.4	27.9	21.0
	$N(E_{\rm F})~({\rm eV}~{\rm cm}^3)^{-1}$	4.02×10^{14}	2.50×10^{15}	5.93×10^{15}
	R_{hop} (nm)	166.7	90.6	68.0
	W (meV)	128.1	128.1	128.1
40 wt%	a_0 (nm)	108.1	50.9	37.9
	$N(E_{\rm F})~({\rm eV}~{\rm cm}^3)^{-1}$	1.88×10^{13}	1.80×10^{14}	4.36×10^{14}
	R_{hop} (nm)	431.7	203.2	151.4
	W (meV)	157.8	157.8	157.8
60 wt%	a_0 (nm)	105.7	50.4	37.5
	$N(E_{\rm F})~({\rm eV}~{\rm cm}^3)^{-1}$	2.00×10^{13}	1.84×10^{14}	4.36×10^{14}
	R_{hop} (nm)	422.6	201.5	150.9
	W (meV)	158.2	158.2	158.2
WO ₃ /PPy	` ,			
40 wt%	a_0 (nm)	125.8	59.7	41.4
	$N(E_{\rm F})~({\rm eV}~{\rm cm}^3)^{-1}$	7.08×10^{14}	6.63×10^{15}	1.99×10^{16}
	R_{hop} (nm)	181.1	85.9	59.5
	W (meV)	56.8	56.8	56.8
60 wt%	a_0 (nm)	148.6	67.7	48.9
	$N(E_{\rm F})~({\rm eV}~{\rm cm}^3)^{-1}$	7.37×10^{14}	7.78×10^{15}	2.08×10^{16}
	R_{hop} (nm)	186.9	85.2	61.4
	W (meV)	49.6	49.6	49.6

and Fe₃O₄/PPy nanocomposites [28]. The calculated W is observed to be H independent and has no change with increasing H. Meanwhile, from Tables 1 and 2, it can be obtained that different polymer matrix with the same WO₃ nanoparticle loadings has different Mott parameters including T_0 , R_{hop} and W, and the WO₃/PANI nanocomposites have a lower a_0 and $N(E_F)$, and higher R_{hop} and W compared with those of the WO₃/PPy nanocomposites.

4. Conclusion

In summary, the WO₃/PANI and WO₃/PPy nanocomposites exhibit different crystallinity at the same WO₃ nanoparticle loading. The conductive disordered WO₃/PANI and WO₃/PPy nanocomposites have been demonstrated to follow 3-d variable range hopping mechanism by the temperature dependent resistivity study. The observed positive MR is interpreted by the wave-function shrinkage model and well explained by the introduced a_0 , $N(E_{\rm F})$ and $R_{\rm hop}$. The conductive polymer matrices have shown different effects on the MR behaviors of the nanocomposites and the WO₃/PANI nanocomposites have an lower a_0 and $N(E_{\rm F})$, and higher $R_{\rm hop}$ and W compared with those of the WO₃/PPy nanocomposites.

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Appendix A. Supplementary data

Supplementary data related to this article can be found at http://dx.doi.org/10.1016/j.polymer.2013.12.024.

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